ESD Protection Diode Low Capacitance Surface Mount ESD Protection for High-Speed Data Interfaces

The LC03-6 surge protection is designed to protect equipment attached to high speed communication lines from ESD, EFT, and lighting.

Features

- SO-8 Package
- Peak Power 2000 Watts 8 x 20 µS
- ITU K.20 $I_{PP} = 40 \text{ A} (5/310 \text{ } \mu\text{s})$
- Bellcore 1089 (Intra-Building) 100 A (2/10 µs)
- ESD Rating: IEC 61000-4-2 (ESD) 15 kV (air) 8 kV (contact) IEC 61000-4-4 (EFT) 40 A (5/50 ns) IEC 61000-4-5 (lighting) 95 A (8/20 μs)
- UL Flammability Rating of 94 V-0
- Pb–Free Package is Available

Typical Applications

• High Speed Communication Line Protection

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation 8 x 20 μS @ T _A = 25°C (Note 1)	P _{pk}	2000	W
Peak Pulse Current (8 x 20 μ S Waveform)	I _{PP}	100	А
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum 10 Seconds Duration	ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse 8 x 20 µS exponential decay waveform



ON Semiconductor®

www.onsemi.com

SO-8 LOW CAPACITANCE VOLTAGE SUPPRESSOR 2 kW PEAK POWER 6 VOLTS



(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
LC03-6R2	SO-8	2500/Tape & Reel
LC03-6R2G	SO–8 (Pb–Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	6.8	-	-	V
Reverse Leakage Current @ V _{RWN} = 5.0 V	I _R	N/A	-	20	μΑ
Maximum Clamping Voltage @ I_{PP} = 50 A, 8 x 20 μS	V _C	N/A	-	15	V
Maximum Clamping Voltage @ I_{PP} = 100 A, 8 x 20 μS	V _C	N/A	-	20	V
Between I/O Pins and Ground @ V _R = 0 V, 1.0 MHz	Capacitance	-	16	25	pF
Between I/O Pins @ V _R = 0 Volts, 1.0 MHz	Capacitance	-	8.0	12	pF



Figure 1. Reverse Voltage versus Temperature



Figure 2. Reverse Leakage versus Temperature



Current

TYPICAL CHARACTERISTICS

LC03-6R2

APPLICATIONS INFORMATION

The LC03–6 ON Semiconductor's device is a surge protection Diode array designed to protect sensitive electronics such as communications systems, computers, and computer peripherals against damage due to transient overvoltage conditions caused by lightning, electrostatic discharge (ESD), and electrical fast transients (EFT). Because of its relative low capacitance (<25 pf), it can be used in high speed I/O data lines such as USB 1.1 ports.

The integrated design of the LC03–6 device offers high surge rating, low capacitance steering diodes, and a surge protection diode integrated in a single package (SO–8). In addition, this device offers compliance to Bellcore 1089 requirements (intra–building).

LC03–6 Device's Configurations Options

Protection of Two High-speed I/O Data Lines

The LC03–6 device is able to protect two high speed data lines against transient overvoltage conditions by driving them to a fixed reference point for clamping purposes. Depending in the application's requirements, the LC03–6 device can be configured for protection in either differential mode (Line–to–Line) or common mode (Line–to–ground). The Figure 5 shows the connection for Differential mode (Line–to–Line) and Common mode (Line–to–Ground) protection. The inputs and outputs of the I/O data lines are connected at terminals 1 to 8, and 4 to 5 while the terminals 2, 3, 6 and 7 are connected to ground; for better performance, it is recommended to minimize parasitic inductances by using ground planes and minimizing the PCB trace lengths for the ground return connections.



Figure 5. Configuration for Differential and Common Mode Protection

If differential protection is required by some particular applications, then the configuration for differential protection is made as shown in the Figure 6:



Figure 6. Configuration for Differential Protection (Line-to-Line)

T1/E1 Linecard Protection (Intra-Building)

The Figure 7 shows a typical schematic for a T1/E1 line card protection circuit. The LC03–6 device is connected between Tip and Ring on the transmit and receive line pairs. it provides protection to metallic and common mode lightning surges per Bellcore 1089 intra–building (For further information, see Bellcore 1089 standard). A metallic voltage is defined as a difference of potential between the T and R terminals of a telecommunications pair. Currents caused by lightning, in the absence of protector operation and with balanced terminal equipment and telecommunications loop, cause Tip and Ring conductors to attain the same potential hence do not produce metallic transients. Common mode surges are suppressed by the isolation of the transformer.



Figure 7. Typical T1 Line Card Protection

ESD Protection in USB 1.1 Port Applications

As we know, a USB port is composed of four lines. The lines D+ and D- are used for bi-directional data transmission, and the remaining two lines are reserved for bus voltage and ground. Since USB is a hot plugging and unplugging system, all its four lines have the risk to receive ESD conditions in the real field of the application.

Typical ESD protection techniques are commonly formed by the combination of different discrete semiconductor products which make this technique obsolete and non–efficient because the interconnections of the discrete devices increase the parasitic inductance effects during a transient condition which reduces significantly the performance of the ESD protection circuit. The LC03–6 device provides a unique surge protection Diode array designed to protect two I/O data lines (single USB port) against damage due to ESD conditions or transient voltage conditions. Because of its low capacitance, it can be used in high speed I/O data lines such as USB 1.1 components. In addition to its low capacitance characteristics, the LC03–6 device from ON Semiconductor complies with the most common industrial standards for ESD, EFT and surge protection: IEC61000–4–2, IEC61000–4–4, IEC61000–4–5.





*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER EMITTER 5. BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6. BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC з COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 COMMON ANODE/GND 8. STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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